

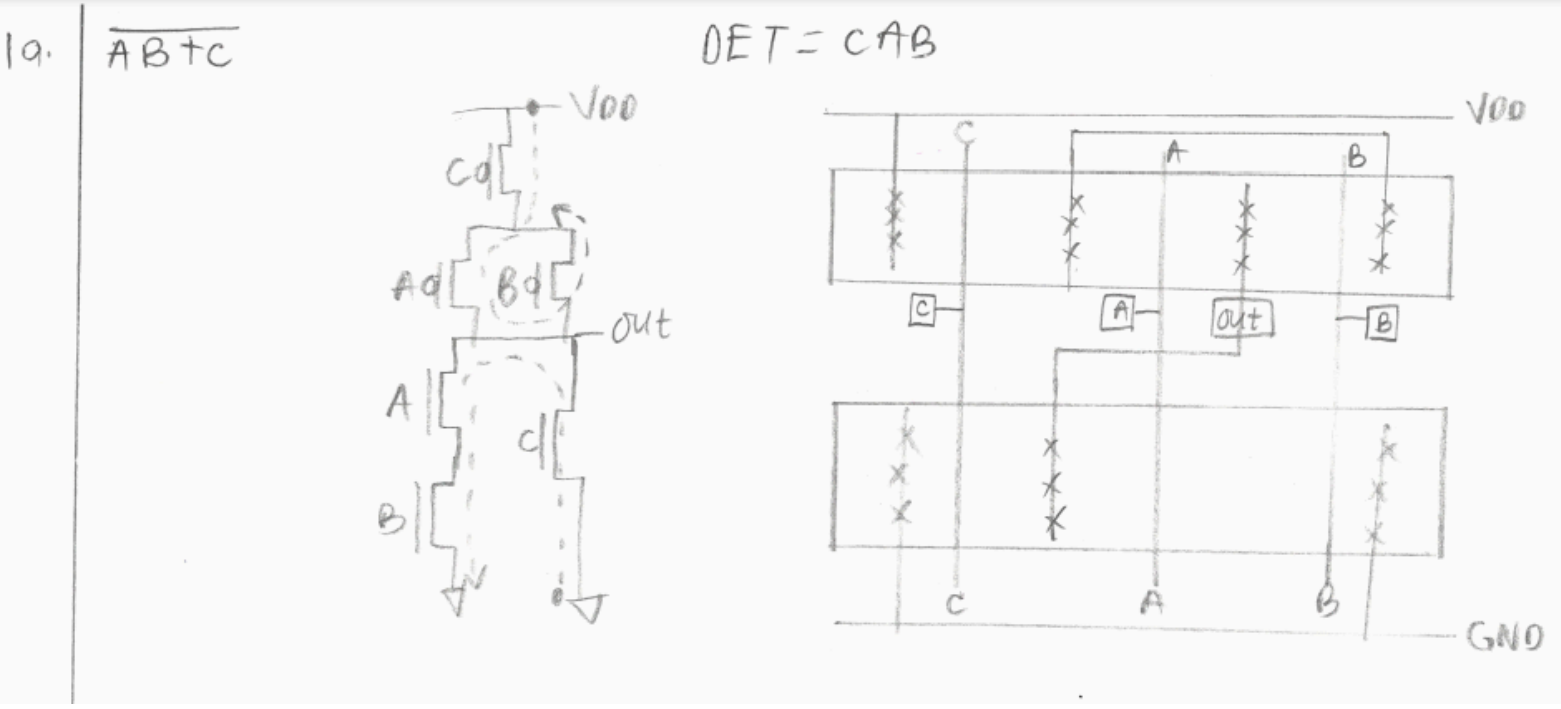
1. Implement the following function:

$$Y = \overline{AB + C}$$

- a) Draw a stick diagram implementing the function in the CMOS logic family.
- b) Draw an optimized schematic of this function implemented in Pass-Transistor Logic (PTL) with an output inverter.
- c) Draw a schematic of the function implemented in pseudo-NMOS.

NMOS: + parallel
 • → series

PMOS: • → parallel
 + → series

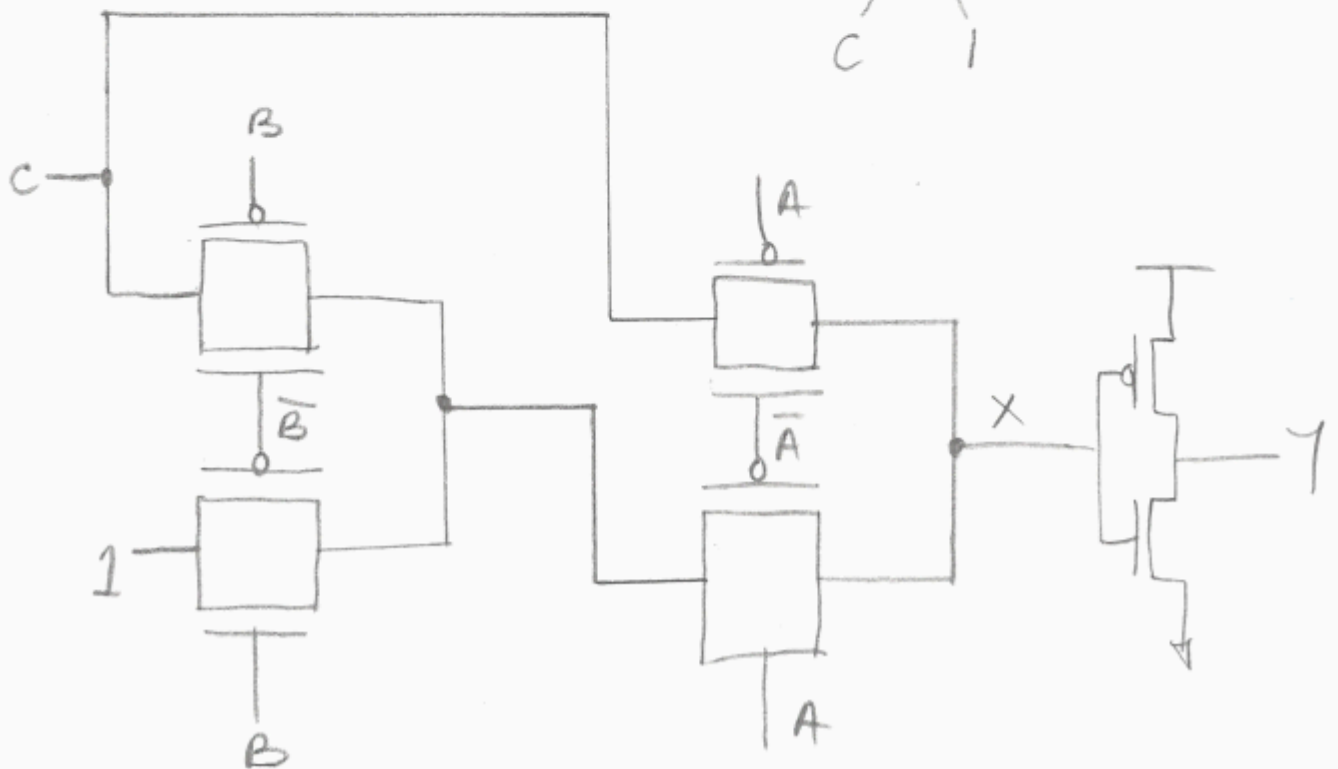
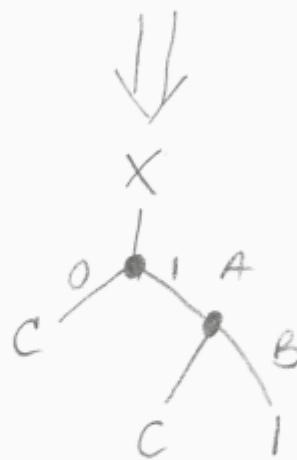


Pass Transistor Logic with an Inverter

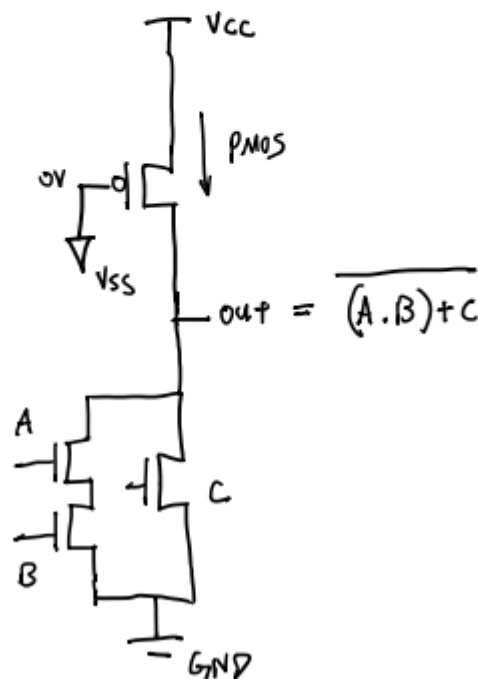
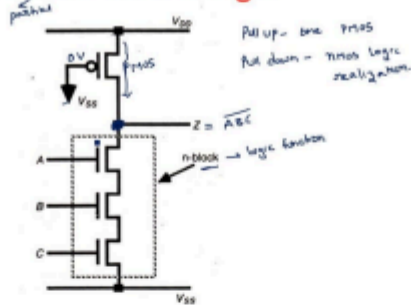
↳ low power circuit
 avoid leakage

b. $Y = \overline{AB + C} \rightarrow X = \overline{Y} = AB + C$

A	B	C	X
0	0	0	0
0	0	1	1
0	1	0	0
0	1	1	1
1	0	0	0
1	0	1	1
1	1	0	1
1	1	1	1



Pseudo nMOS logic



2. For the functions in a and b:

- Draw the schematic that performs the function
- Use **dual Euler paths** to find the minimum number of diffusion breaks, clearly show your work
- Draw **stick diagram** providing best layout with minimum number of diffusion breaks
- Draw the exact corresponding schematic for your layout in 'iii' (if this is same as 'i' don't redraw but mention 'same as i')

a $out = (A + B + C)(D + E(F + G))(H + I)J$

b $out = \overline{ABC + D(E + FG) + HIJK + LM}$

$$(A+B+C)(D+E(F+G)(H+I)J)$$

NMOS: + parallel

pmos \rightarrow parallel

- \rightarrow series

$t \rightarrow$ series

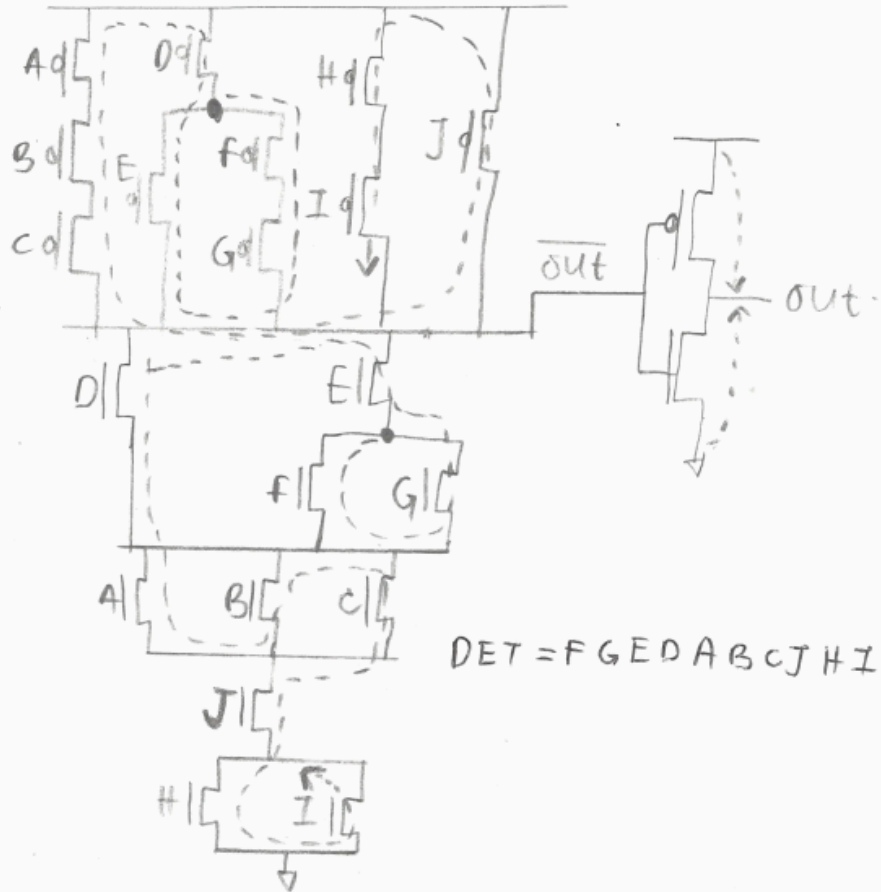
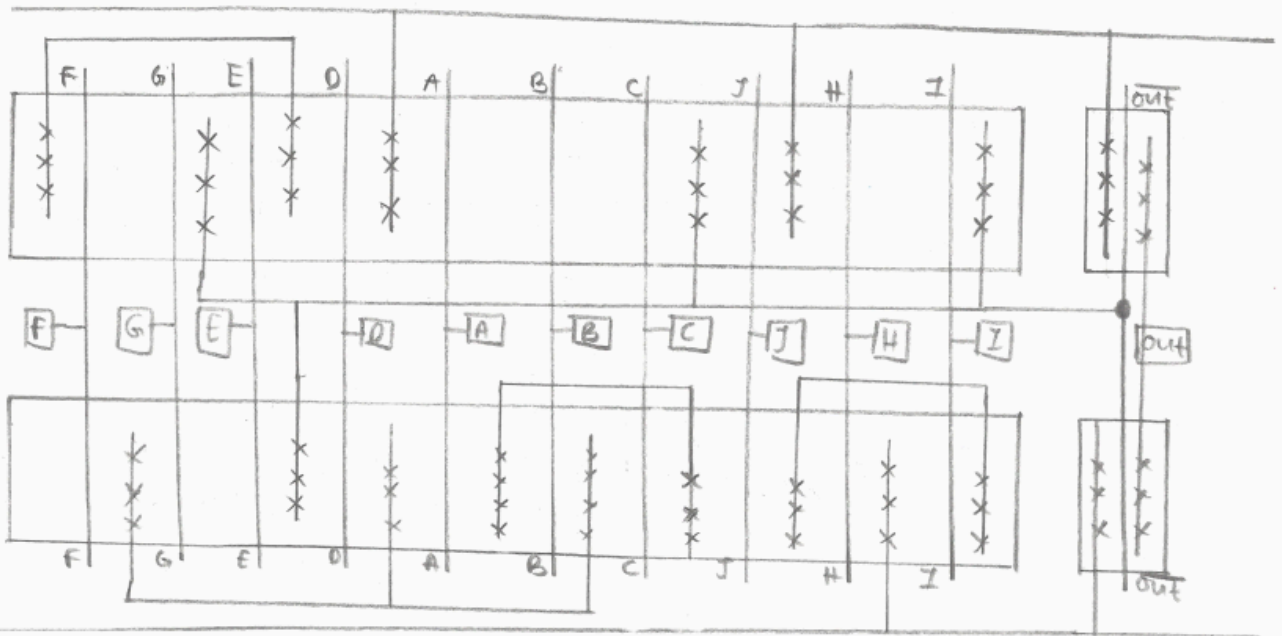
2a.

i

8

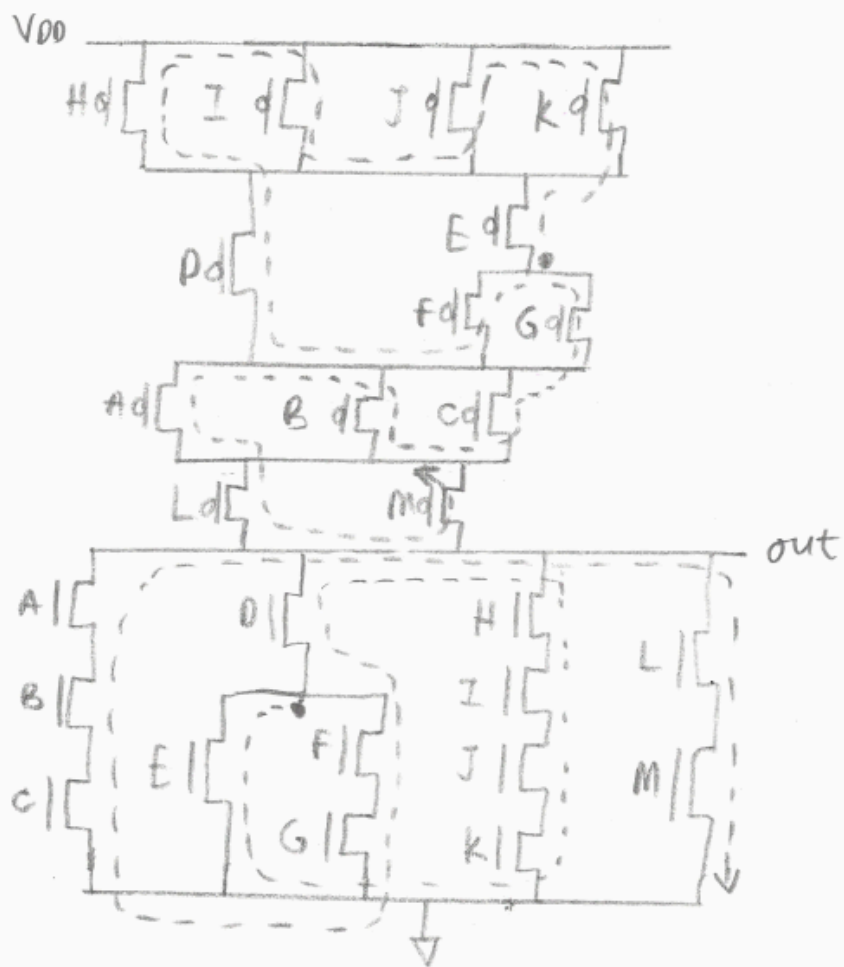
ii

$$\text{Out} = (A+B+C)(D+E(F+G))(H+I)J$$


$$DET = FGEDABCH I // \overline{OUT}$$
 $V \partial \eta$ 

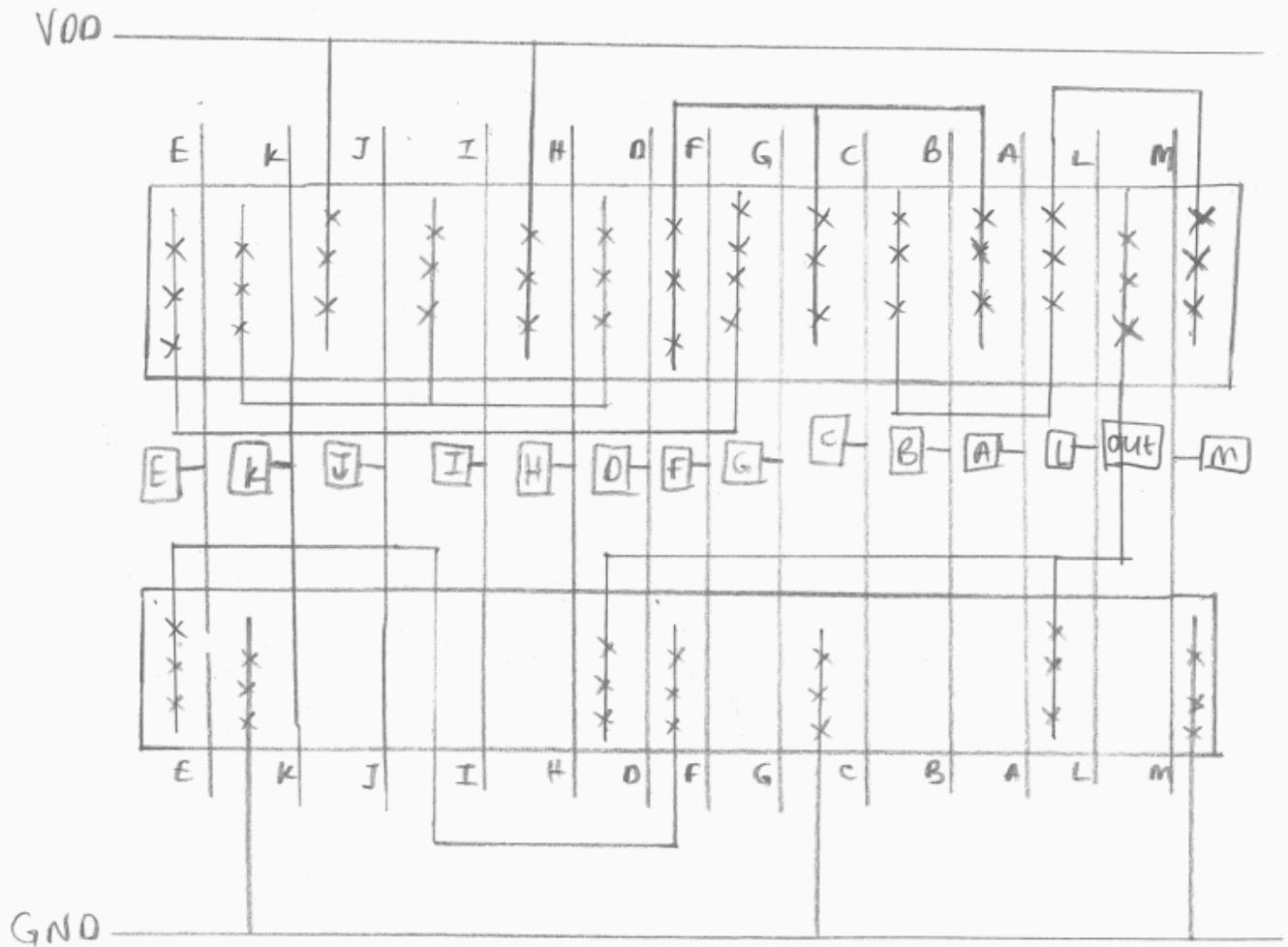
GND

2b.)
i
ii

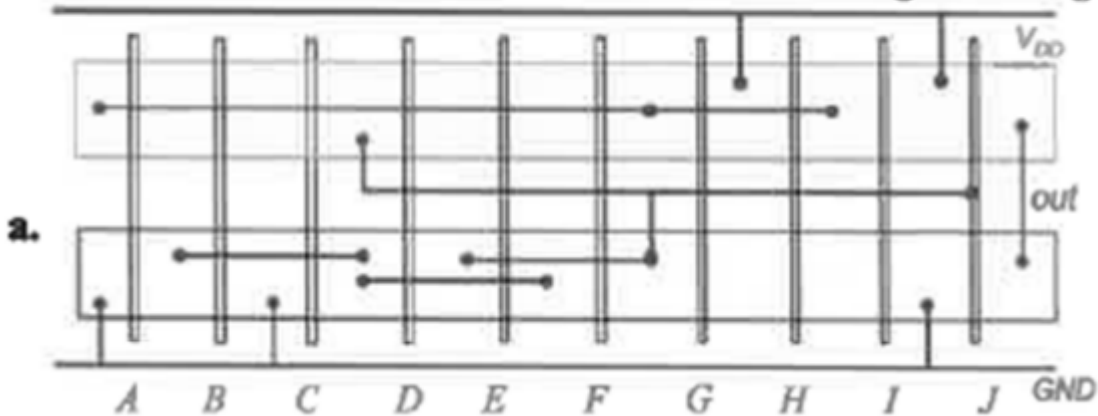


$$DET = EKJIHDFGCBALM$$

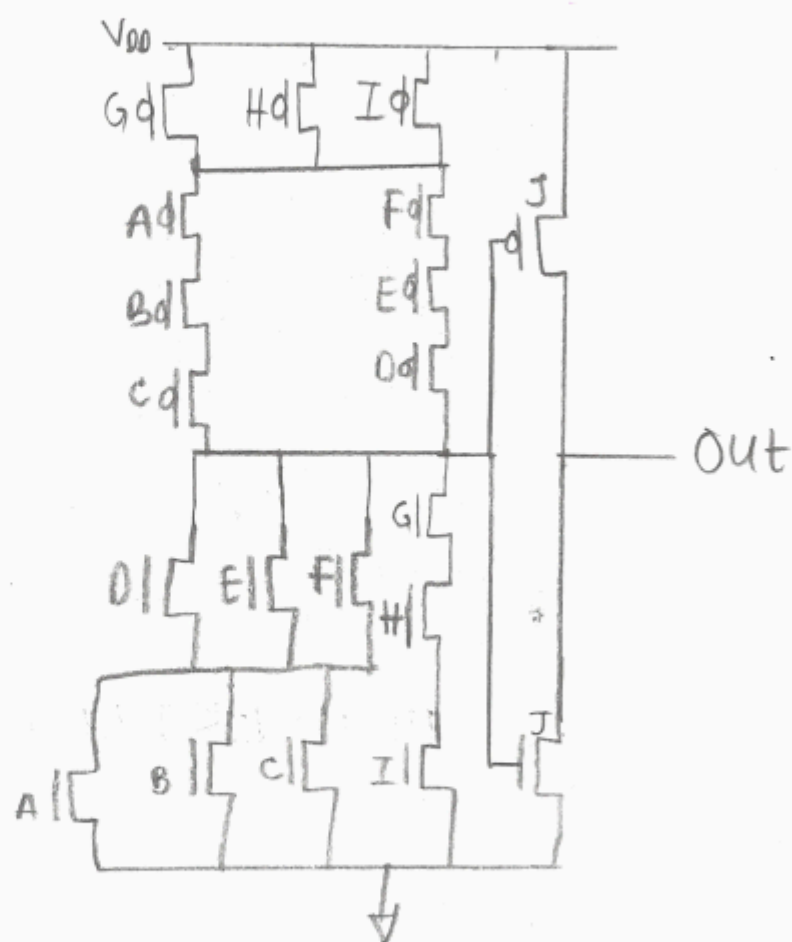
ii



3. Write down the Boolean functions for the following stick diagrams:

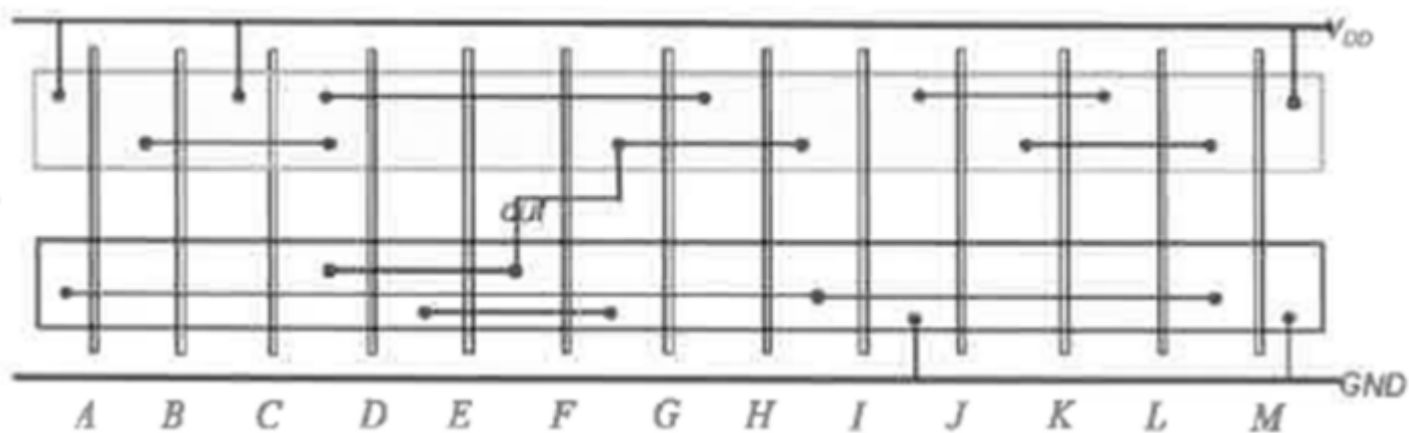


3.
a.

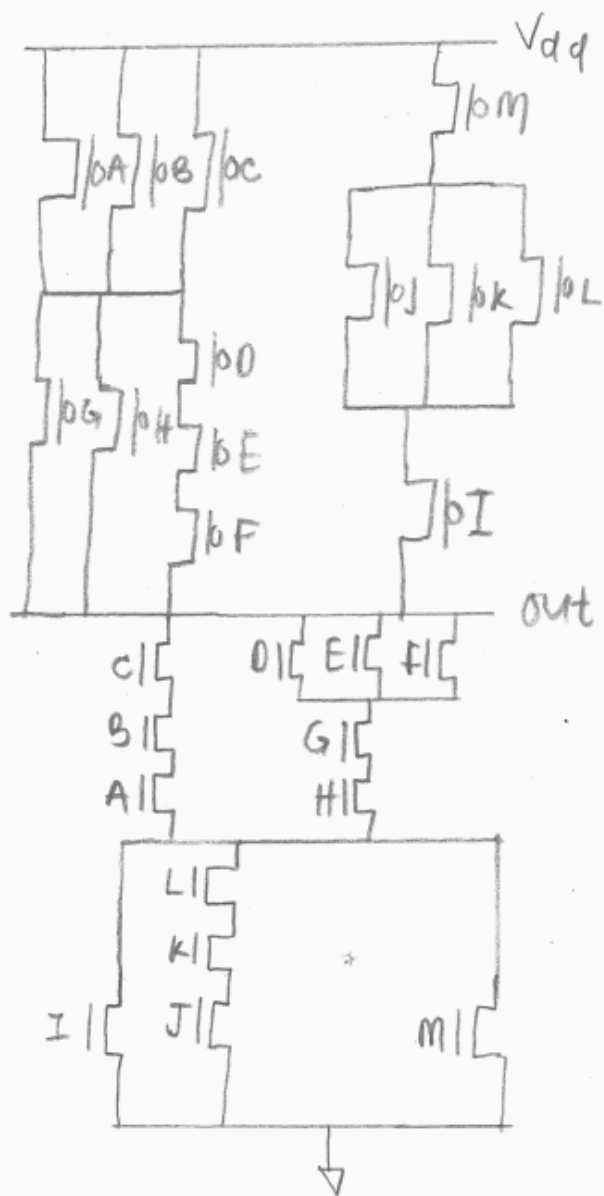


$$\begin{aligned} Out &= \overline{(A+B+C)(D+E+F) + GHI} + inv \\ &= (A+B+C)(D+E+F) + GHI \end{aligned}$$

b.



3b'



$$out = (ABC + (DEF)GH)(I + JKL + M)$$